

FRED

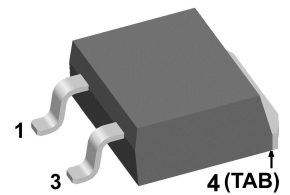
$$\begin{aligned} V_{RRM} &= 1200 \text{ V} \\ I_{FAV} &= 12 \text{ A} \\ t_{rr} &= 50 \text{ ns} \end{aligned}$$

Fast Recovery Epitaxial Diode Single Diode

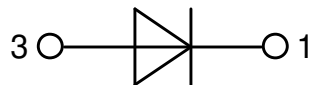
Part number

DSEI12-12AZ

Marking on Product: DSEI12-12AZ



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-263 (D2Pak-HV)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

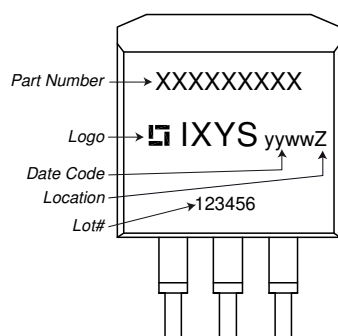
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Fast Diode				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V	
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				1200	V	
I _R	reverse current, drain current	V _R = 1200 V	T _{VJ} = 25°C			250	μA	
		V _R = 960 V	T _{VJ} = 125°C			4	mA	
V _F	forward voltage drop	I _F = 12 A	T _{VJ} = 25°C			2.58	V	
		I _F = 24 A				2.94	V	
		I _F = 12 A	T _{VJ} = 150°C			2.23	V	
		I _F = 24 A				2.72	V	
I _{FAV}	average forward current	T _C = 100°C rectangular d = 0.5	T _{VJ} = 150°C			12	A	
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 150°C		1.77	V	
r _F	slope resistance					38	mΩ	
R _{thJC}	thermal resistance junction to case					1.6	K/W	
R _{thCH}	thermal resistance case to heatsink				0.25		K/W	
P _{tot}	total power dissipation	T _C = 25°C				78	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		75	A	
C _J	junction capacitance	V _R = 600 V f = 1 MHz		T _{VJ} = 25°C	6		pF	
I _{RM}	max. reverse recovery current	} I _F = 11 A; V _R = 540 V -di _F /dt = 100 A/μs		T _{VJ} = 25 °C	4		A	
				T _{VJ} = 100 °C	6		A	
t _{rr}	reverse recovery time			T _{VJ} = 25 °C	150		ns	
				T _{VJ} = 100 °C	300		ns	

Package TO-263 (D2Pak-HV)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			25	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				1.5		g
F_C	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	4.2			mm
$d_{Spb/Apb}$		terminal to backside	4.7			mm

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI12-12AZ-TRL	DSEI12-12AZ	Tape & Reel	800	515338
Alternative	DSEI12-12AZ-TUB	DSEI12-12AZ	Tube	50	525375

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$



Fast Diode

$V_{0\max}$ threshold voltage

1.77

V

$R_{0\max}$ slope resistance *

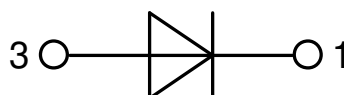
35

mΩ

Outlines TO-263 (D2Pak-HV)


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.3		0.091	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with and/or within JEDEC standard.



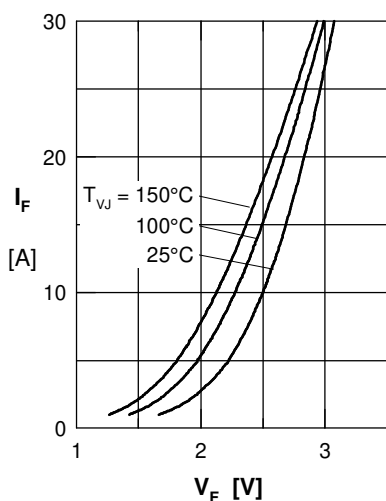
Fast Diode


Fig. 1 Forward current I_F versus max. forward voltage drop V_F

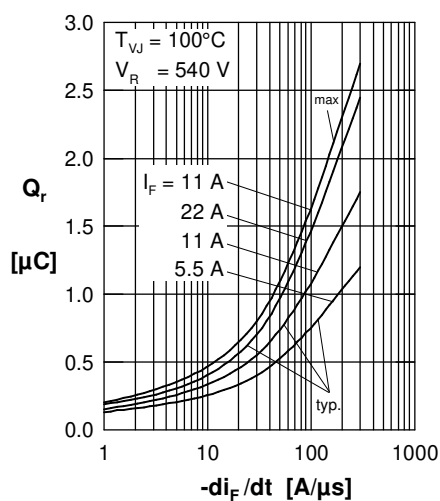


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

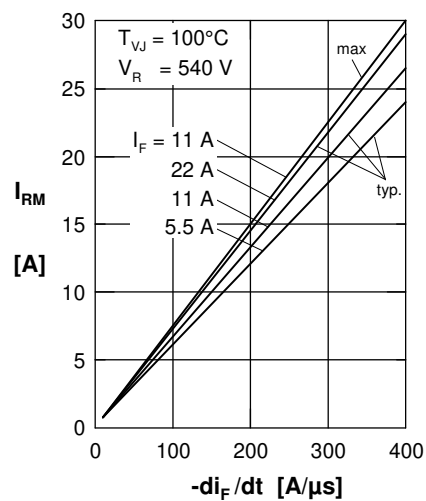


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

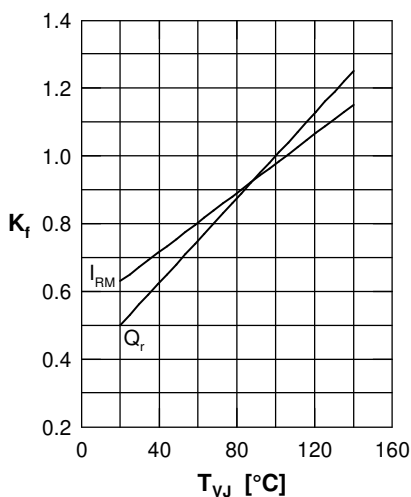


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

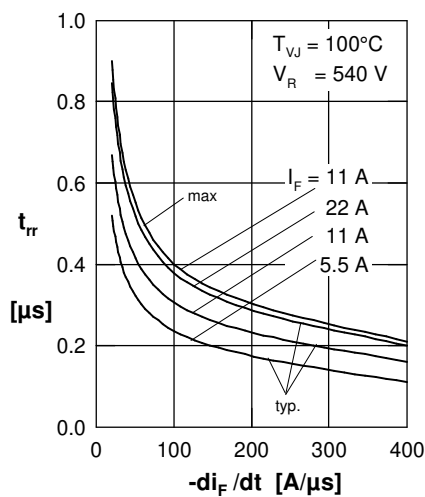


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

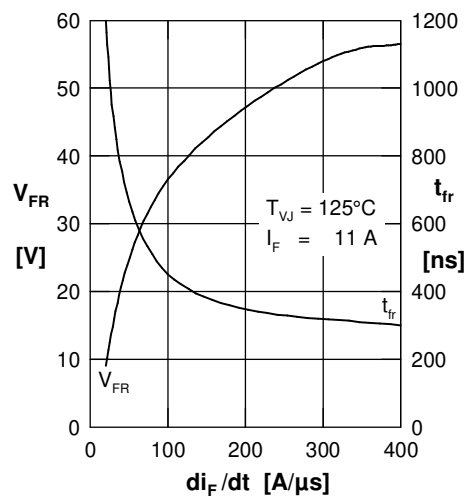


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

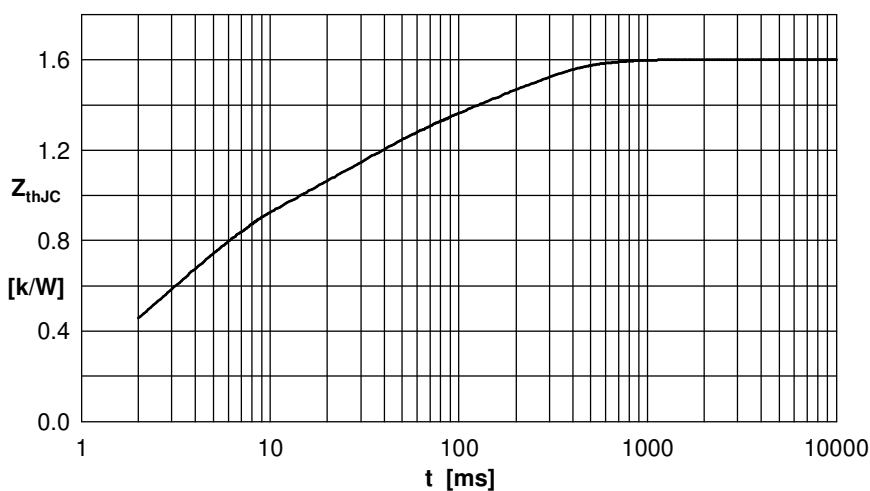


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.100	0.001
2	0.020	0.010
3	0.400	0.180
4	0.400	0.024
5	0.680	0.003